



Docket No.: M4065.0900/P900
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ramin Ghodsi

Application No.: 10/822,785

Confirmation No.: 3196

Filed: April 13, 2004

Art Unit: 2824

For: MULTI-CELL RESISTIVE MEMORY
ARRAY ARCHITECTURE WITH SELECT
TRANSISTOR

Examiner: E. J. Wendler

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated January 10, 2006, please amend the above-identified U.S. patent application as follows:

Amendments to the Drawings are identified at page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 12 of this paper.